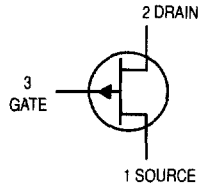
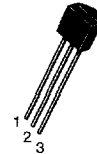


JFET Amplifiers
P-Channel — Depletion



2N5460
2N5461
2N5462



CASE 29-04, STYLE 7
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain- Gate Voltage	V_{DG}	40	Vdc
Reverse Gate- Source Voltage	V_{GSR}	40	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Junction Temperature Range	T_J	-65 to +135	$^\circ\text{C}$
Storage Channel Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Gate-Source Breakdown Voltage ($I_G = 10 \mu\text{Adc}$, $V_{DS} = 0$)	2N5460, 2N5461, 2N5462	$V_{(BR)GSS}$	40	—	—	Vdc
Gate Reverse Current ($V_{GS} = 20 \text{ Vdc}$, $V_{DS} = 0$) ($V_{GS} = 30 \text{ Vdc}$, $V_{DS} = 0$) ($V_{GS} = 20 \text{ Vdc}$, $V_{DS} = 0$, $T_A = 100^\circ\text{C}$) ($V_{GS} = 30 \text{ Vdc}$, $V_{DS} = 0$, $T_A = 100^\circ\text{C}$)	2N5460, 2N5461, 2N5462 2N5460, 2N5461, 2N5462	I_{GSS}	—	—	5.0 1.0	nAdc μAdc
Gate-Source Cutoff Voltage ($V_{DS} = 15 \text{ Vdc}$, $I_D = 1.0 \mu\text{Adc}$)	2N5460 2N5461 2N5462	$V_{GS(off)}$	0.75 1.0 1.8	— — —	6.0 7.5 9.0	Vdc
Gate-Source Voltage ($V_{DS} = 15 \text{ Vdc}$, $I_D = 0.1 \text{ mAdc}$) ($V_{DS} = 15 \text{ Vdc}$, $I_D = 0.2 \text{ mAdc}$) ($V_{DS} = 15 \text{ Vdc}$, $I_D = 0.4 \text{ mAdc}$)	2N5460 2N5461 2N5462	V_{GS}	0.5 0.8 1.5	— — —	4.0 4.5 6.0	Vdc

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ kHz}$)	2N5460 2N5461 2N5462	I_{DSS}	-1.0 -2.0 -4.0	— — —	-5.0 -9.0 -16	mAdc
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SMALL-SIGNAL CHARACTERISTICS

Forward Transfer Admittance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ kHz}$)	2N5460 2N5461 2N5462	$ y_{fs} $	1000 1500 2000	— — —	4000 5000 6000	μmhos
Output Admittance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ kHz}$)		$ y_{os} $	—	—	75	μmhos
Input Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)		C_{iss}	—	5.0	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)		C_{rss}	—	1.0	2.0	pF

FUNCTIONAL CHARACTERISTICS

Noise Figure ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $R_G = 1.0 \text{ Megohm}$, $f = 100 \text{ Hz}$, $BW = 1.0 \text{ Hz}$)		NF	—	1.0	2.5	dB
Equivalent Short-Circuit Input Noise Voltage ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 100 \text{ Hz}$, $BW = 1.0 \text{ Hz}$)		e_n	—	60	115	$\text{nV}/\sqrt{\text{Hz}}$

DRAIN CURRENT versus GATE SOURCE VOLTAGE

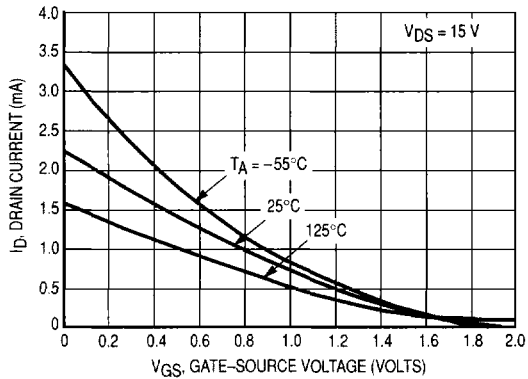


Figure 1. $V_{GS(off)} = 2.0$ Volts

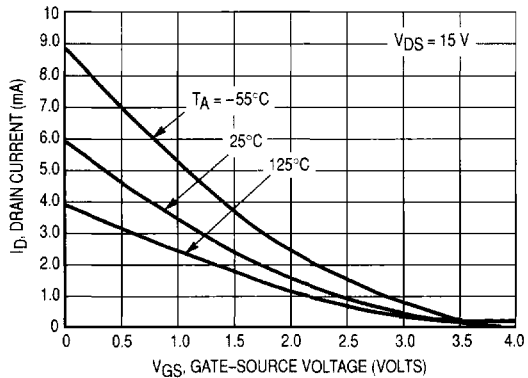


Figure 2. $V_{GS(off)} = 4.0$ Volts

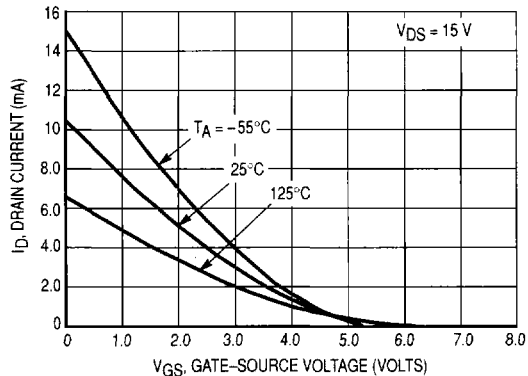


Figure 3. $V_{GS(off)} = 5.0$ Volts

FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

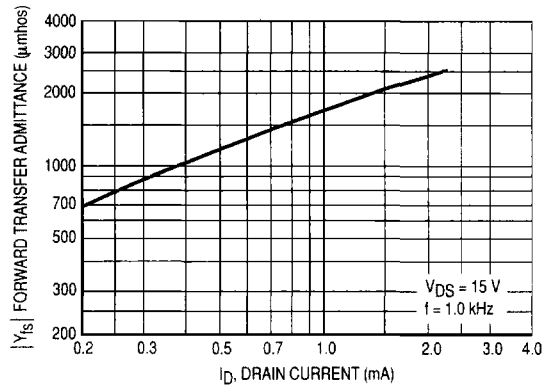


Figure 4. $V_{GS(off)} = 2.0$ Volts

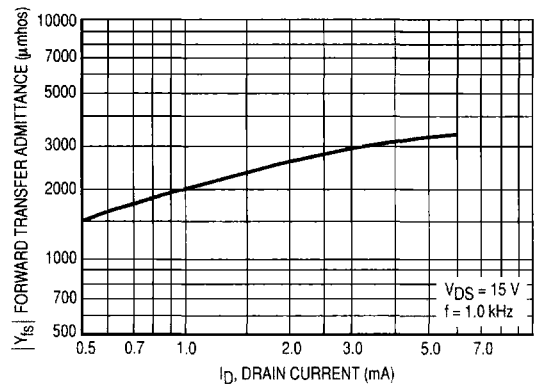


Figure 5. $V_{GS(off)} = 4.0$ Volts

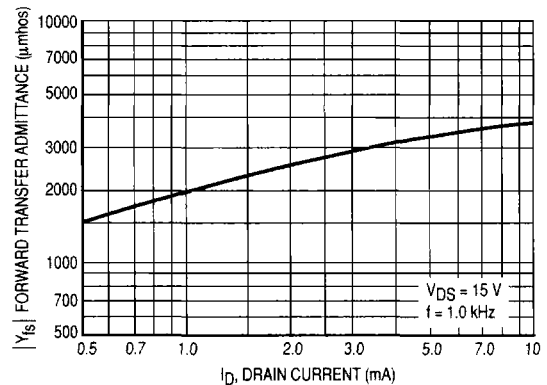


Figure 6. $V_{GS(off)} = 5.0$ Volts

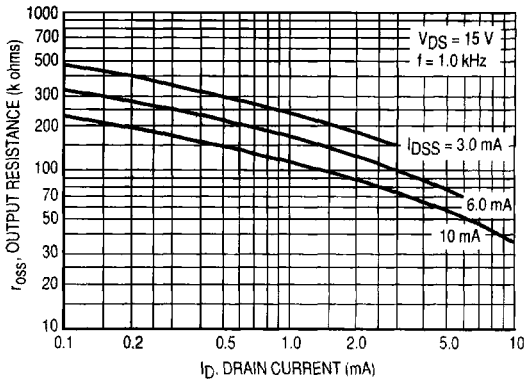


Figure 7. Output Resistance versus Drain Current

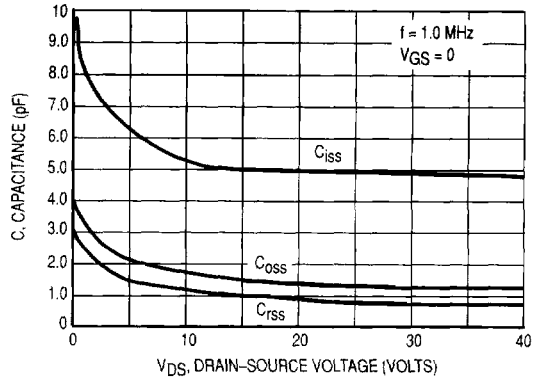


Figure 8. Capacitance versus Drain-Source Voltage

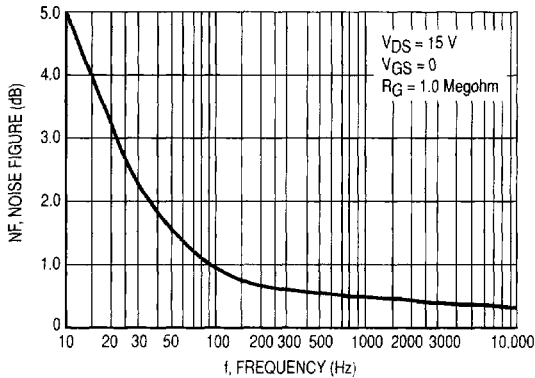


Figure 9. Noise Figure versus Frequency

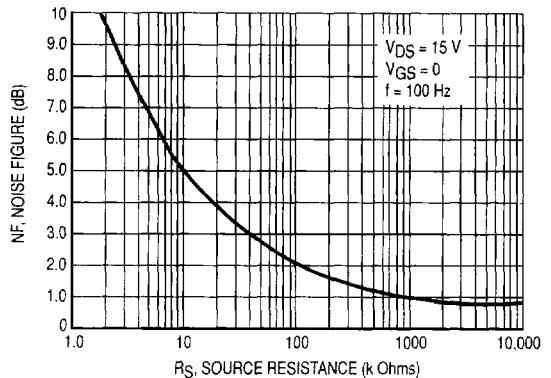
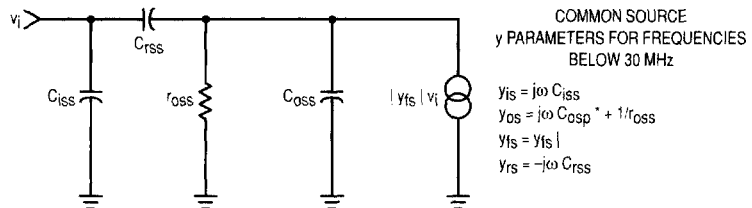


Figure 10. Noise Figure versus Source Resistance



* C_{osp} is C_{oss} in parallel with Series Combination of C_{iss} and C_{rss} .

NOTE:

- Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

Figure 11. Equivalent Low Frequency Circuit